TEXAS INSTRUMENTS

TPD2E2U06

SLLSEG9B – JUNE 2013 – REVISED MAY 2015

TPD2E2U06 Dual-Channel High-Speed ESD Protection Device

1 Features

- IEC 61000-4-2 Level 4
  - ±25 kV (Contact Discharge)
  - ±30 kV (Air-gap Discharge)
- IEC 61000-4-5 Surge Protection
  - 5.5 A Peak Pulse Current (8/20 µs Pulse)
- IO Capacitance 1.5 pF (Typ)
- DC Breakdown Voltage 6.5 V (Min)
- Ultra-Low Leakage Current 10 nA (Max)
- Low ESD Clamping Voltage
- Industrial Temperature Range: –40°C to +125°C
- Small Easy-to-Route DRL Package

2 Applications

- End Equipment
  - Set Top Box
  - Notebook
  - Server
  - Electronic Point of Sale (EPOS)
- Interfaces
  - USB 2.0
  - Ethernet
  - MIPI Bus
  - LVDS
  - I2C

3 Description

The TPD2E2U06 is a dual-channel low capacitance TVS diode ESD protection device. The device offers ±25-kV contact and ±30-kV air-gap ESD protection in accordance with the IEC 61000-4-2 standard. The 1.5-pF line capacitance of the TPD2E2U06 makes the device suitable for a wide range of applications. Typical application interfaces are USB 2.0, LVDS, and I^{2}C™.

Device Information[1]

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TPD2E2U06	SOT (5)	1.60 mm × 1.20 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.
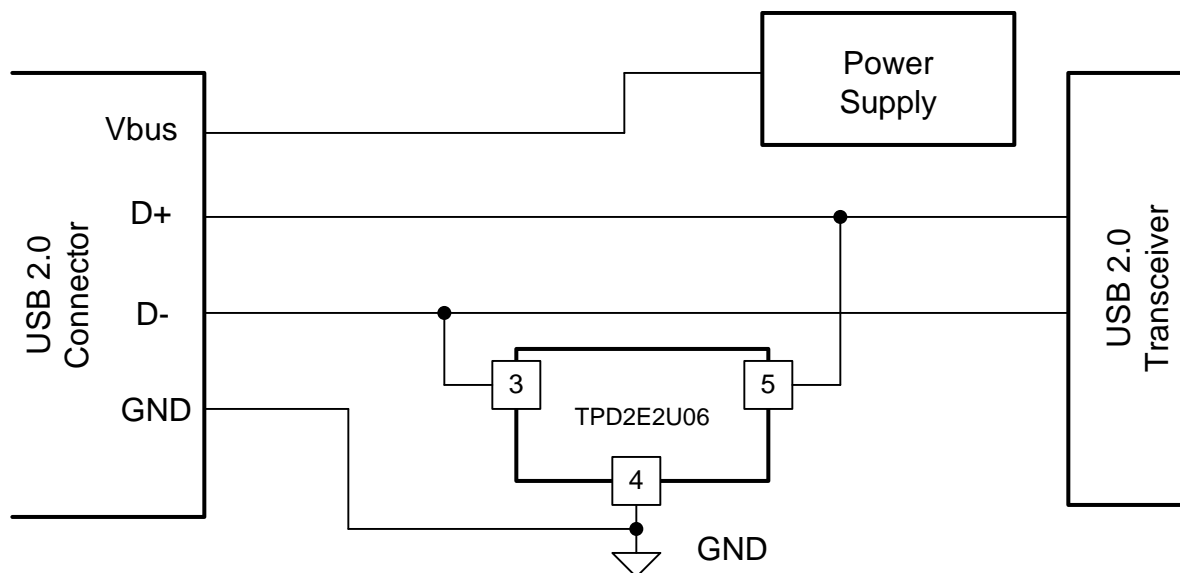
4 Simplified Schematic

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## 5 Revision History

Changes from Revision A (June 2013) to Revision B   **Page**

* Added ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section. 1

6 Pin Configuration and Functions

DRL
1.65 mm × 1.2 mm × 0.6 mm
(0.5-mm PITCH)
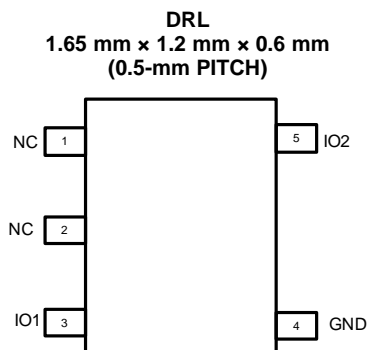
Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
IO1	3	I/O	The IO1 and IO2 pins are an ESD protected channel. Connect these pins to the data line as close to the connector as possible.
IO2	5	I/O	
NC	1, 2	-	This pin is not connected and is left floating, grounded, or connected to VCC.
GND	4	G	The GND (ground) pin is connected to ground.

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
I_{PP}	Peak pulse current (tp = 8/20 µs)		5.5[1]	A
P_{PP}	Peak pulse power (tp = 8/20 µs)		85[1]	W
	Operating temperature	−40	125	°C
	Storage temperature	−65	155	°C

(1) Measured at 25°C.

7.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001[1]	±4000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101[2]	±1500	
		EC 61000-4-2 contact	±25000	
		EC 61000-4-2 air-gap	±30000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 500-V HBM is possible with the necessary precautions.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 250-V CDM is possible with the necessary precautions.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{IO}	Input Pin Voltage	0		5.5	V
T_A	Operating Free Air Temperature	-40		125	°C

7.4 Thermal Information

THERMAL METRIC[1]		TPD2E2U06	UNIT
		DRL	
		5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	286.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	130.7	
$R_{\theta JB}$	Junction-to-board thermal resistance	104.8	
ψ_{JT}	Junction-to-top characterization parameter	25.6	
ψ_{JB}	Junction-to-board characterization parameter	104.3	

(1)　For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.

7.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{RWM}	Reverse stand-off voltage	$I_{IO} < 10$ µA			5.5	V
V_{CLAMP}	IO to GND	$I_{PP} = 1$ A, TLP[1]		9.7		V
		$I_{PP} = 5$ A, TLP[1]		12.4		
V_{CLAMP}	GND to IO	$I_{PP} = 1$ A, TLP[1]		1.9		V
		$I_{PP} = 5$ A, TLP[1]		4		
R_{DYN}	Dynamic resistance	IO to GND[2]		0.5		Ω
R_{DYN}	Dynamic resistance	GND to IO[2]		0.25		Ω
CL	Line capacitance	f = 1 MHz, $V_{BIAS} = 2.5$ V[3]		1.5	1.9	pF
C_{CROSS}	Channel-to-channel input capacitance	Pin 4 = 0 V, f = 1 MHz, $V_{BIAS} = 2.5$ V, between channel pins[3]		0.02	0.03	pF
$\Delta_{CIO-TO-GND}$	Variation of channel input capacitance	Pin 4 = 0 V, f = 1 MHz, $V_{BIAS} = 2.5$ V, channel_x pin to GND – channel_y pin to GND[3]		0.03	0.1	pF
V_{BR}	Break-down voltage	$I_{IO} = 1$ mA	6.5		8.5	V
I_{LEAK}	Leakage current	$V_{IO} = 2.5$ V		1	10	nA

(1)　Transmission Line Pulse with 10-ns rise time, 100-ns width.
(2)　Extraction of R_{DYN} Using least squares fit of TLP characteristics between I = 20 A and I = 30 A.
(3)　Measured at 25°C.
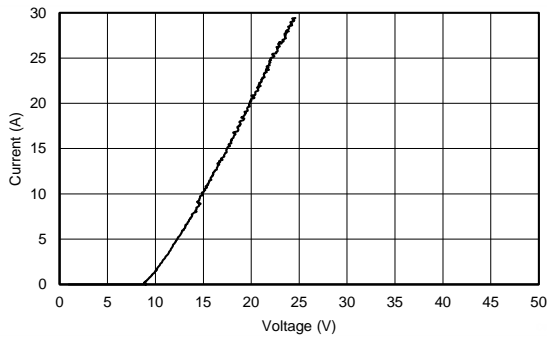
7.6 Typical Characteristics
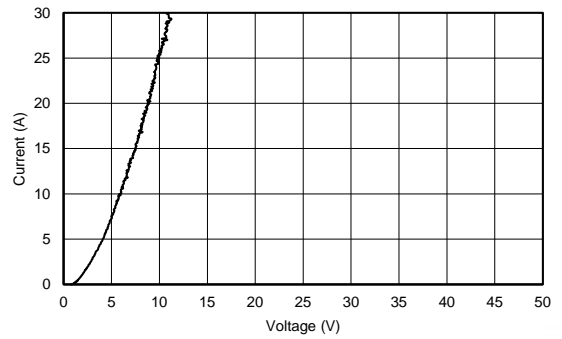

Figure 1. TLP, Data to GND
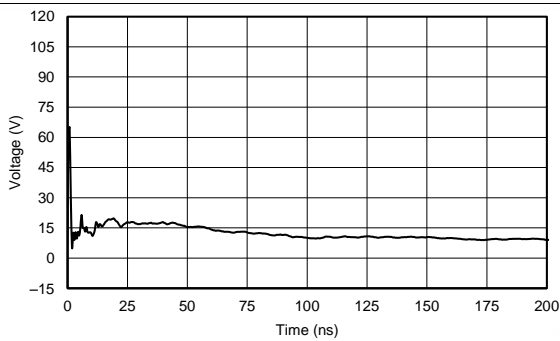

Figure 2. TLP, GND to Data

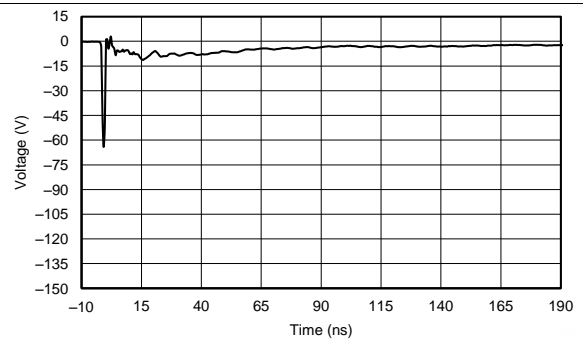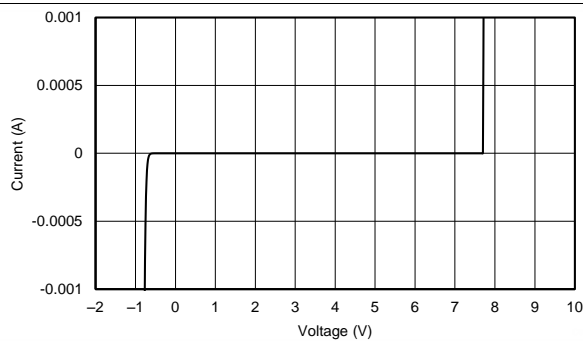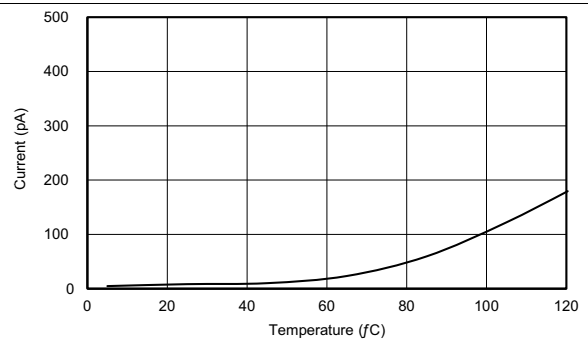**Figure 3. IEC 61000-4-2 Clamping Voltage, +8 kV Contact**

Figure 4. IEC 61000-4-2 Clamping Voltage, –8 kV Contact

T_A = 25°C

Figure 5. IV Curve

V_{IN} 2.5 V

Figure 6. I_{LEAK} vs Temperature
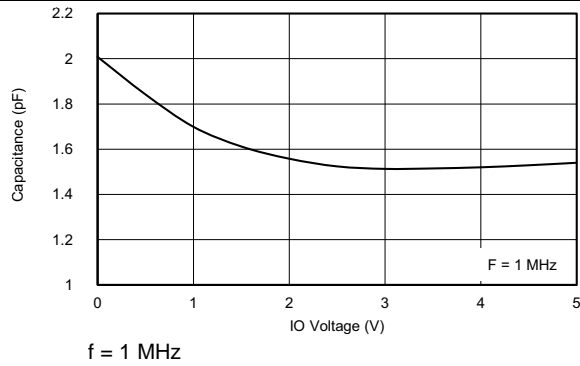
Typical Characteristics (continued)

f = 1 MHz

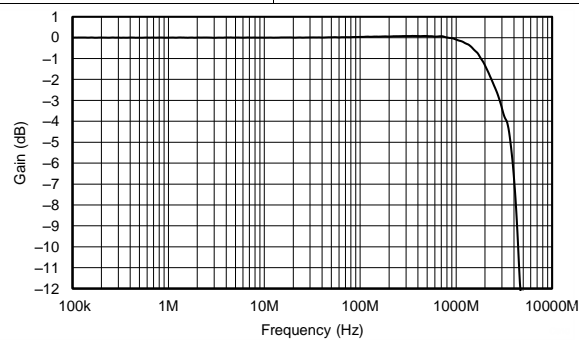**Figure 7. Capacitance Across V_BIAS**
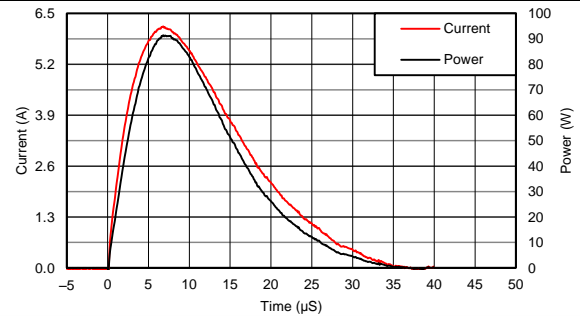
**Figure 8. Surge Curve (tp = 8/20 µs) IO to GND**

Figure 9. Insertion Loss

8 Detailed Description

8.1 Overview

The TPD2E2U06 is a dual-channel low capacitance TVS diode ESD protection device. The device offers ±25-kV contact and ±30-kV air-gap ESD protection in accordance with the IEC 61000-4-2 standard. The 1.5-pF line capacitance of the TPD2E2U06 makes the device suitable for a wide range of applications. Typical application interfaces are USB 2.0, LVDS, and I2C.

8.2 Functional Block Diagram
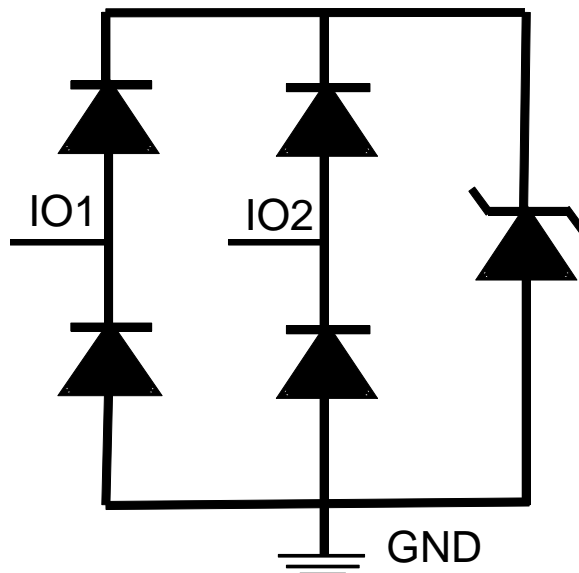
8.3 Feature Description

The TPD2E2U06 is a dual-channel low capacitance TVS diode ESD protection device. The device offers ±25-kV contact and ±30-kV air-gap ESD protection in accordance with the IEC 61000-4-2 standard. The 1.5-pF line capacitance of the TPD2E2U06 makes the device suitable for a wide range of applications. Typical application interfaces are USB 2.0, LVDS, and I2C.

8.3.1 IEC 61000-4-2 Level 4

The I/O pins can withstand ESD events up to ±25-kV contact and ±30-kV air. An ESD/surge clamp diverts the current to ground.

8.3.2 IO Capacitance

The capacitance between each I/O pin to ground is 1.5 pF. These capacitances support data rates in excess of 1.5 Gbps.

8.3.3 DC Breakdown Voltage

The DC breakdown voltage of each I/O pin is a minimum of 6.5 V. This ensures that sensitive equipment is protected from surges above the reverse standoff voltage of 5.5 V.

8.3.4 Ultra-Low Leakage Current

The I/O pins feature an ultra-low leakage current of 10 nA (Max) with a bias of 2.5 V.

8.3.5 Low ESD Clamping Voltage

The I/O pins feature an ESD clamp that is capable of clamping the voltage to 9.7 V (I_{PP} = 1 A).

Feature Description (continued)

8.3.6 Industrial Temperature Range

This device is designed to operate from –40°C to 125°C.

8.3.7 Small Easy-to-Route Package

The layout of this device makes it simple and easy to add protection to an existing layout. The packages offers flow-through routing, requiring minimal modification to an existing layout.

8.4 Device Functional Modes

TPD2E2U06 is a passive integrated circuit that triggers when voltages are above V_{BR} or below the lower diodes V_f (–0.6 V). During ESD events, voltages as high as ±30 kV (air) can be directed to ground via the internal diode network. Once the voltages on the protected line fall below the trigger levels of TPD2E2U06 (usually within 10's of nano-seconds) the device reverts to passive.

Product Folder Links: *TPD2E2U06*

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

TPD2E2U06 is a diode type TVS which is typically used to provide a path to ground for dissipating ESD events on hi-speed signal lines between a human interface connector and a system. As the current from ESD passes through the TVS, only a small voltage drop is present across the diode. This is the voltage presented to the protected IC. The low R_{DYN} of the triggered TVS holds this voltage, V_{CLAMP}, to a safe level for the protected IC.

9.2 Typical Application
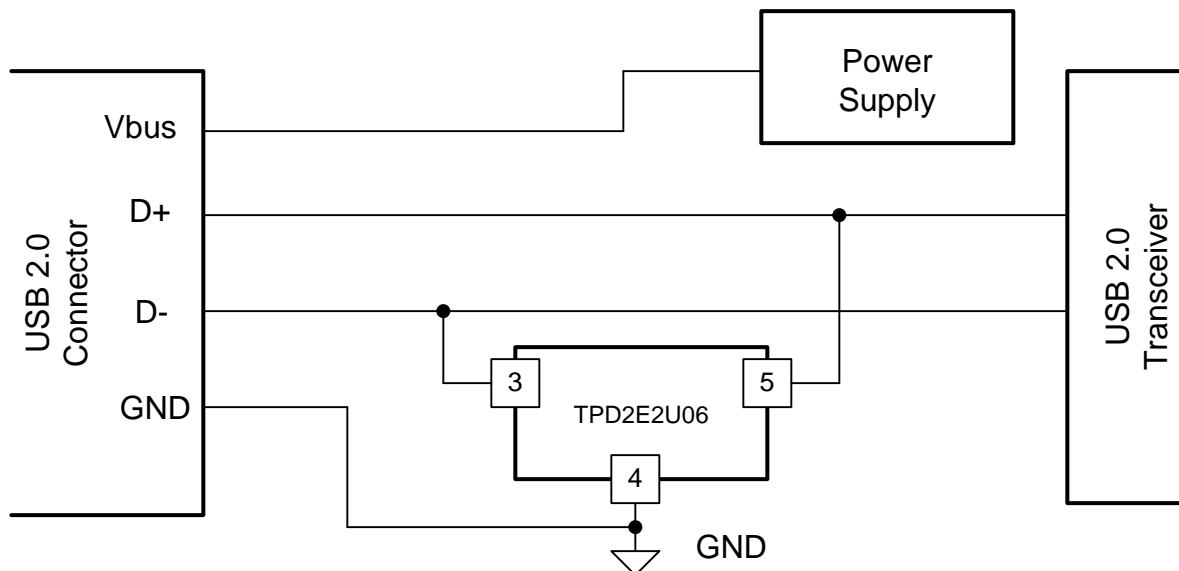
Figure 10. Typical USB Application Diagram

9.2.1 Design Requirements

For this design example, one TPD2E2U06 device will be used in a USB 2.0 application. This will provide complete port protection.

Given the USB 2.0 application, the following parameters are known.

DESIGN PARAMETER	VALUE
Signal range on Pins 3 or 5	0 V to 3.3 V
Operating Frequency	240 MHz

9.2.2 Detailed Design Procedure

To begin the design process, some parameters must be decided upon; the designer needs to know the following:
- Signal range of all the protected lines
- Operating frequency

9.2.2.1 Signal Range

The TPD2E2U06 has 2 identical protection channels for signal lines. The symmetry of the device provides flexibility when selecting which of the 2 I/O channels will protect which signal lines. Any I/O will support a signal range of 0 to 5.5 V.

9.2.2.2 Operating Frequency

The TPD2E2U06 has a capacitance of 1.5 pF (Typ), supporting USB 2.0 data rates.

9.2.3 Application Curves

Figure 11. Insertion Loss Graph
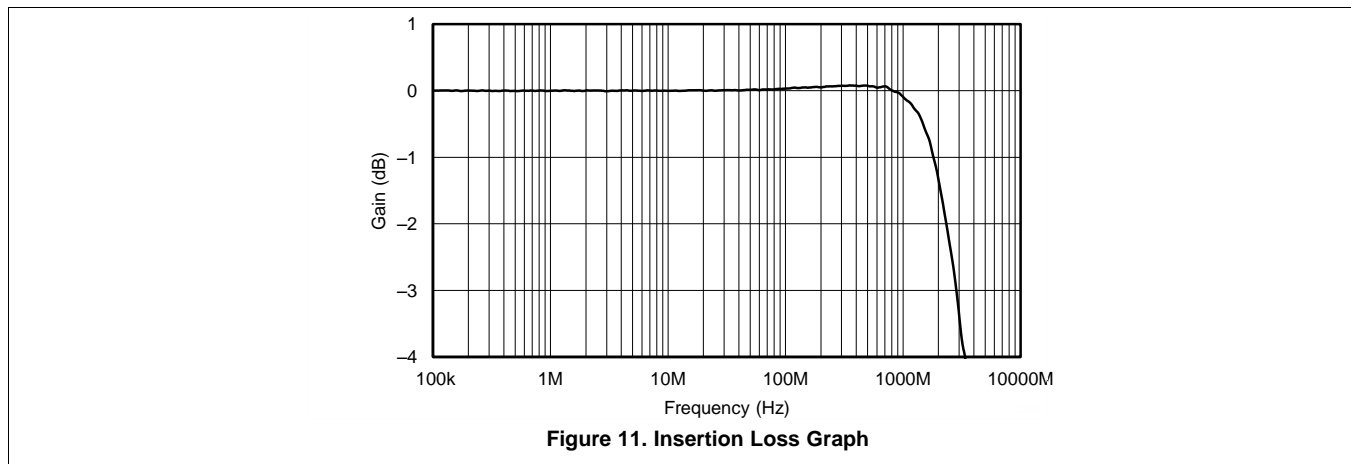
10 Power Supply Recommendations

This device is a passive ESD protection device and there is no need to power it. Care should be taken to make sure that the maximum voltage specifications for each line are not violated.

11 Layout

11.1 Layout Guidelines

- The optimum placement is as close to the connector as possible.
  - EMI during an ESD event can couple from the trace being struck to other nearby unprotected traces, resulting in early system failures.
  - The PCB designer needs to minimize the possibility of EMI coupling by keeping any unprotected traces away from the protected traces which are between the TVS and the connector.
- Route the protected traces as straight as possible.
- Eliminate any sharp corners on the protected traces between the TVS and the connector by using rounded corners with the largest radii possible.
  - Electric fields tend to build up on corners, increasing EMI coupling.

11.2 Layout Example

$\bigcirc$ = VIA to GND
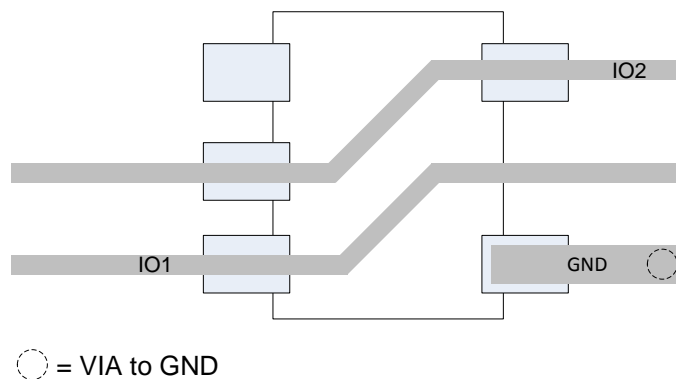
Figure 12. Routing with DRL Package

12 Device and Documentation Support

12.1 Trademarks

I^{2}C is a trademark of NXP Semiconductors.
All other trademarks are the property of their respective owners.

12.2 Electrostatic Discharge Caution

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.3 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGE OPTION ADDENDUM

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPD2E2U06DRLR	ACTIVE	SOT-5X3	DRL	5	4000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	DT	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF TPD2E2U06 :

● Automotive: TPD2E2U06-Q1

NOTE: Qualified Version Definitions:

● Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

PACKAGE MATERIALS INFORMATION

TAPE AND REEL INFORMATION

REEL DIMENSIONS

TAPE DIMENSIONS

A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPD2E2U06DRLR	SOT-5X3	DRL	5	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPD2E2U06DRLR	SOT-5X3	DRL	5	4000	183.0	183.0	20.0

A

$\frac{1,70}{1,50}$

5X $\frac{0,27}{0,13}$

B

5   4

C

$\frac{1,30}{1,10}$

$\frac{1,70}{1,50}$

Pin 1 Index Area

1   2   3

0,50

5X $\frac{0,25}{0,15}$

⊕	0,10 Ⓜ	C	A	B
	0,05 Ⓜ	C		

$\frac{0,60}{0,50}$

⌒ 0,05 C

Seating Plane

C

$\frac{0,05}{0,00}$

$\frac{0,18}{0,08}$

1   2   3

5X $\frac{0,40}{0,20}$

5   4

Bottom View

4205622−2/D   08/2007

NOTES: A.   All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M−1994.
          B.   This drawing is subject to change without notice.
        C   Body dimensions do not include mold flash, interlead flash, protrusions, or gate burrs.
              Mold flash, interlead flash, protrusions, or gate burrs shall not exceed 0,15 per end or side.
          D.   JEDEC package registration is pending.

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IMPORTANT NOTICE